



Product Specifications

PART NO:

VL374S3323-GA/GH/GLS

REV: 1.0

General Information

256MB 32Mx72 SDRAM PC100/PC133 UNBUFFERED ECC 168 PIN DIMM

Description: The VL374S3323 is a 32Mx72 Synchronous Dynamic RAM high density memory module. This memory module consists of eighteen CMOS 16Mx8 bits with 4 banks Synchronous DRAMs in TSOP-II 400 mil packages and a 2K EEPROM in 8-pin TSSOP package on a 168 pin glass-epoxy substrate. Two 0.1uF decoupling capacitors are mounted on the printed circuit board for each SDRAM. This module is a dual in-line memory module and is intended for mounting into 168 pin edge connector sockets. Synchronous design allows precise cycle control with the use of system clock. I/O transactions are possible on every clock cycle. Range of operating frequencies, programmable latencies allows the same device to be useful for a variety of high bandwidth, high performance memory system applications.

Features:

- Unbuffered 8 byte SDRAM 168pin DIMM
- High Speed - 100MHz, 133MHz , CL2, CL3
- Burst Mode Operation
- Auto & Self refresh Capability (4096 Cycles/64ms)
- LVTTTL compatible inputs and outputs
- Single 3.3V ±0.3 V power supply
- 12/10/4 Addressing (Row/Column/Bank)
- MRS cycle with address key programs
Latency (Access from column address)
Burst length (1, 2, 4, 8 & Full page)
Data scramble (Sequential & Interleave)
- All inputs are sampled at the positive going edge of the system clock
- EPROM Serial Presence Detect
- PCB height: **1158 (mil)**, double sided component
- Gold (Au) contacts
- Lead-free/RoHS complaint

Pin Name	Function
A0-A11	Address inputs
BA0, BA1	Bank Select Address
DQ0-DQ63	Data Input/Output
CLK0-CLK3	Clock Input
CKE0-CKE1	Clock Enable Input
CS0#-CS3#	Chip Select Input
CB0-CB7	Check bits for ECC
RAS#	Row Address Strobe
CAS#	Column Address Input
WE#	Write Enable
DQM0-DQM7	Data input/output mask
VDD	Power Supply (3.3V)
VSS	Ground
*VREF	Power Supply for Reference
SDA	Serial Data Input/Output
SCL	SPD Clock Input
SA0 - SA2	Address in EEPROM
NC	No Connect
* These pins are not used in this module.	

Order Information:

VL374S3323-GA S X

DRAM DIE (Option)

DRAM MANUFACTURER
S - SAMSUNG

MODULE SPEED
GA: PC133 @ CL3
GH: PC100 @ CL2
GL: PC100 @ CL3

VL: Lead-free/RoHS



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Pin Configuration

Pin Number	Front Side	Pin Number	Front Side	Pin Number	Back Side	Pin Number	Back Side
1	V _{SS}	43	V _{SS}	85	V _{SS}	127	V _{SS}
2	DQ0	44	NC	86	DQ32	128	CKE0
3	DQ1	45	CS2#	87	DQ33	129	CS3#
4	DQ2	46	DQM2	88	DQ34	130	DQM6
5	DQ3	47	DQM3	89	DQ35	131	DQM7
6	V _{DD}	48	NC	90	V _{DD}	132	NC
7	DQ4	49	V _{DD}	91	DQ36	133	V _{DD}
8	DQ5	50	NC	92	DQ37	134	NC
9	DQ6	51	NC	93	DQ38	135	NC
10	DQ7	52	CB2	94	DQ39	136	CB6
11	DQ8	53	CB3	95	DQ40	137	CB7
12	V _{SS}	54	V _{SS}	96	V _{SS}	138	V _{SS}
13	DQ9	55	DQ16	97	DQ41	139	DQ48
14	DQ10	56	DQ17	98	DQ42	140	DQ49
15	DQ11	57	DQ18	99	DQ43	141	DQ50
16	DQ12	58	DQ19	100	DQ44	142	DQ51
17	DQ13	59	V _{DD}	101	DQ45	143	V _{DD}
18	V _{DD}	60	DQ20	102	V _{DD}	144	DQ52
19	DQ14	61	NC	103	DQ46	145	NC
20	DQ15	62	NC	104	DQ47	146	NC
21	CB0	63	CKE1	105	CB4	147	NC
22	CB1	64	V _{SS}	106	CB5	148	V _{SS}
23	V _{SS}	65	DQ21	107	V _{SS}	149	DQ53
24	NC	66	DQ22	108	NC	150	DQ54
25	NC	67	DQ23	109	NC	151	DQ55
26	V _{DD}	68	V _{SS}	110	V _{DD}	152	V _{SS}
27	WE#	69	DQ24	111	CAS#	153	DQ56
28	DQM0	70	DQ25	112	DQM4	154	DQ57
29	DQM1	71	DQ26	113	DQM5	155	DQ58
30	CS0#	72	DQ27	114	CS1#	156	DQ59
31	NC	73	V _{DD}	115	RAS#	157	V _{DD}
32	V _{SS}	74	DQ28	116	V _{SS}	158	DQ60
33	A0	75	DQ29	117	A1	159	DQ61
34	A2	76	DQ30	118	A3	160	DQ62
35	A4	77	DQ31	119	A5	161	DQ63
36	A6	78	V _{SS}	120	A7	162	V _{SS}
37	A8	79	CLK2	121	A9	163	CLK3
38	A10/AP	80	NC	122	BA0	164	NC
39	BA1	81	N/C	123	A11	165	SA0
40	V _{DD}	82	SDA	124	V _{DD}	166	SA1
41	V _{DD}	83	SCL	125	CLK1	167	SA2
42	CLK0	84	V _{DD}	126	NC	168	V _{DD}



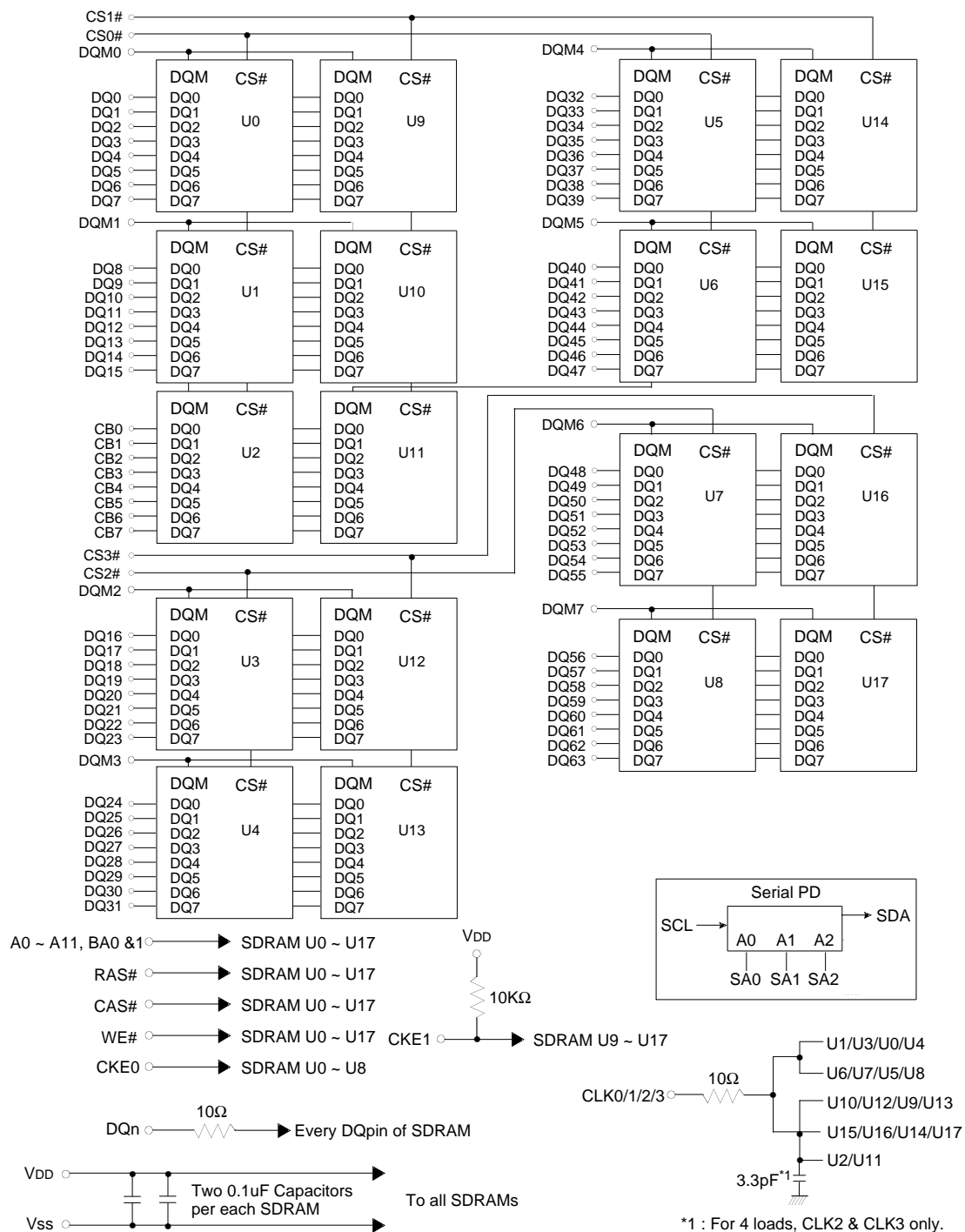
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Functional Block Diagram





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Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Voltage on any pin relative to Vss	V _{IN} , V _{OUT}	-1.0 ~ 4.6	V
Voltage on V _{DD} supply relative to Vss	V _{DD} , V _{DDQ}	-1.0 ~ 4.6	V
Storage temperature	T _{STG}	-55 ~ +150	°C
Power dissipation	P _D	18	W
Short circuit current	I _{OS}	50	mA

Note: Permanent device damage may occur if "ABSOLUTE MAXIMUM RATINGS" are exceeded. Functional operation should be restricted to recommended operating condition. Exposure to higher than recommended voltage for extended periods of time could affect device reliability.

Recommended DC Operating Conditions (T_A = 0°C to +70°C)

Parameter	Symbol	Min	Typ	Max	Unit	Note
Supply voltage	V _{DD} , V _{DDQ}	3.0	3.3	3.6	V	
Input high voltage	V _{IH}	2.0	3.0	V _{DDQ} +0.3	V	1
Input low voltage	V _{IL}	-0.3	0	0.8	V	2
Output high voltage	V _{OH}	2.4	-	-	V	I _{OH} = -2mA
Output low voltage	V _{OL}	-	-	0.4	V	I _{OL} = 2mA
Input leakage current (Inputs)	I _{IL}	-10	-	10	µA	3

Notes: 1. V_{IH} (max) = 5.6V AC. The overshoot voltage duration is ≤ 3ns.
 2. V_{IL} (min) = 2.0V AC. The undershoot voltage duration is ≤ 3ns.
 3. Any input 0V ≤ V_{IN} ≤ V_{DDQ}.

Capacitance (T_A = 25°C, f = 1MHz, V_{DD} = 3.3V)

Parameter	Symbol	Min	Max	Unit
Input capacitance (A0 ~ A11, BA0 ~ BA1)	C _{IN1}	50	95	pF
Input capacitance (RAS#, CAS#, WE#)	C _{IN2}	50	95	pF
Input capacitance (CKE0, CKE1)	C _{IN3}	28	50	pF
Input capacitance (CLK0 ~ CLK3)	C _{IN4}	18	25	pF
Input capacitance (CS0# ~ CS3#)	C _{IN5}	18	30	pF
Input capacitance (DQM0 ~ DQM7)	C _{IN6}	13	20	pF
Data input/output capacitance (DQ0 ~ DQ63)	C _{OUT}	13	18	pF



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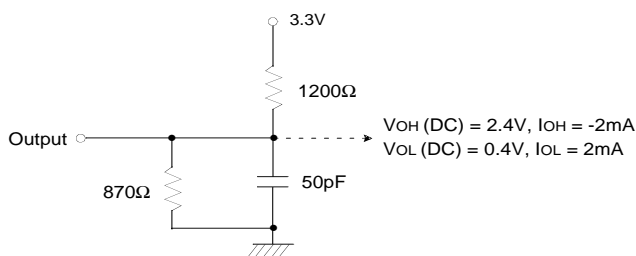
VL374S3323-GA/GH/GLS

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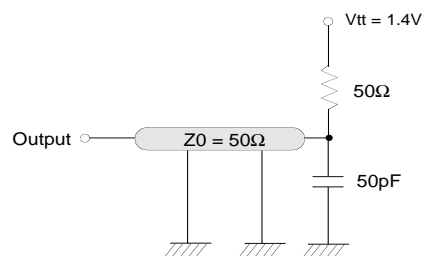
DC Characteristics (Recommended operation condition unless otherwise noted, TA = 0°C to +70°C)							
Parameter	Symbol	Test Condon	Version			Unit	Note
			-GA	-GH	-GL		
Operating current (One bank active)	Icc1	Burst length = 1 trc >= trc(min) IOL = 0 mA	1080	1080	1080	mA	1
Precharge standby current in power-down mode	Icc2P	CKE <= VIL(max), tcc = 10ns	36			mA	
	Icc2PS	CKE & CLK <= VIL(max), tcc = 00	36			mA	
Precharge standby current in non power-down mode	Icc2N	CKE >= VIH (min), CS# >= VIH (min), tcc = 10ns Input signals are changed one time during 20ns	360			mA	
	Icc2NS	CKE >= VIH(min), CLK <= VIL(max), tcc = 00 Input signals are stable	180			mA	
Active standby current in power- down mode	Icc3P	CKE <= VIL(max), tcc = 10ns	90			mA	
	Icc3PS	CKE & CLK <= VIL(max), tcc = 00	90			mA	
Active standby current in non power-down mode (One bank active)	Icc3N	CKE >= VIH(min), CS# >= VIH(min), tcc = 10ns Input signals are changed one time during 20ns	540			mA	
	Icc3NS	CKE >= VIH(min), CLK <= VIL (max), tcc = 00 Input signals are stable	450			mA	
Operating current (Burst mode)	Icc4	IOL = 0 mA Page burst 2 Banks actived tccD = 2CLKs	1260	1170	1170	mA	1
Refresh current	Icc5	trc >= trc(min)	2070	1980	1980	mA	2
Self refresh current	Icc6	CKE <= 0.2V	36			mA	
Note: 1. Measured with outputs open. 2.Refresh period is 64ms.							

AC Operating Test Conditions (VDD = 3.3V, TA = 0°C to +70°C)

Parameter	Value	Unit
AC input levels (V _H /V _L)	2.4/0.4	V
Input timing measurement reference level	1.4	V
Input rise and fall time	tr/ff = 1/1	ns
Output timing measurement reference level	1.4	V
Output load condition	See Fig.2	



(Fig. 1) DC output load circuit



(Fig. 2) AC output load circuit

Operating AC Parameter

Parameter	Symbol	Version			Unit	Note
		-GA	-GH	-GL		
Row active to row active delay	t _{RRD} (min)	15	20	20	ns	1
RAS# to CAS# delay	t _{RCD} (min)	20	20	20	ns	1
Row precharge time	t _{RP} (min)	20	20	20	ns	1
Row active time	t _{RAS} (min)	45	50	50	ns	1
	t _{RAS} (max)	100			us	
Row cycle time	t _{RC} (min)	65	70	70	ns	1
Last data in to row precharge	t _{RDL} (min)	2			CLK	2
Last data in to Active delay	t _{DAL} (min)	2 CLK + t _{RP}			-	
Last data in to new col. address delay	t _{CDL} (min)	1			CLK	1
Last data in to burst stop	t _{BDL} (min)	1			CLK	2
Col. address to col. address delay	t _{CCD} (min)	1			CLK	2
Number of valid output data	CAS Latency = 3	2			CLK	3
	CAS Latency = 2	1			ea	4

Notes: 1. The minimum number of clock cycles is determined by dividing the minimum time required with clock cycle time and then rounding off to the next higher integer.
 2. Minimum delay is required to complete write.
 3. All parts allow every cycle column address change.
 4. In case of row precharge interrupt, auto precharge and read burst stop.



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Operating AC Parameter

Parameter		Symbol	-GA		-GH		-GL		Unit	Note
			Min	Max	Min	Max	Min	Max		
CLK cycle time	CAS latency = 3	tcc	7.5	1000	-	1000	10	1000	ns	1
	CAS latency = 2		-		10		-			
CLK to valid output delay	CAS latency = 3	tsac		5.4		-		6	ns	1,2
	CAS latency = 2			-		6		-		
Output data hold time	CAS latency = 3	toH	3		-		3		ns	2
	CAS latency = 2		-		3		-			
CLK high pulse width		tCH	2.5		3		3		ns	3
CLK low pulse width		tCL	2.5		3		3		ns	3
Input setup time		tSS	1.5		2		2		ns	3
Input hold time		tSH	0.8		1		1		ns	3
CLK to output in Low-Z		tsLZ	1		1		1		ns	2
CLK to output in Hi-z	CAS latency = 3	tSHZ		5.4		-		6	ns	
	CAS latency = 2			-		6		-		

Notes: 1. Parameters depend on programmed CAS latency.
 2. If clock rising time is longer than 1ns, (tr/2-0.5)ns should be added to the parameter.
 3. Assumed input rise and fall time (tr & tf) = 1ns.
 if tr & tf is longer than 1ns, transient timecompensation should be considered,
 i.e. ,[(tr + tf)/2-1]ns should be added to the parameter.



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Revision History:

Date	Rev.	Page	Changes
03/14/2011	1.0	All	Released spec